

Amendments to the Claims

1. (*Currently Amended*) A semiconductor device including a semiconductor body (10) comprising a source region (13) and a drain region (14, 14a) of a first conductivity type, having therebetween a channel-accommodating region (15), the drain region comprising a drain drift region (14) and a drain contact region (14a), with the drain drift region between the channel-accommodating region and the drain contact region, and the drain drift region being doped to a lesser degree than the drain contact region, an insulated gate (11) separated from the channel-accommodating region (15) by a gate insulating layer (17), and a localized region (20, 36, 50) in the drain drift region (14a) juxtaposed with the channel-accommodating region (15), the localized region (20, 36, 50) comprising alternating stripes (31, 32) of the first conductivity type and a second, opposite conductivity type, which stripes extend laterally alongside the channel accommodating region (15) and away from the gate (11), the dimensions and doping levels of the stripes being such that the localized region provides a voltage-sustaining space-charge zone when depleted.
2. (*Currently Amended*) A device of claim 1, wherein the localised region (20, 36, 50) adjoins the channel-accommodating region.
3. (*Currently Amended*) A device of claim 1, wherein the localised region (20, 36, 50) is laterally spaced from the gate insulating layer.
4. (*Currently Amended*) A device of claim 1, 2 A device of claim 1, wherein the average doping level of the localized region (20, 36, 50) is substantially the same as that of an adjacent portion of the drain drift region.
5. (*Currently Amended*) A device of claim 1, 2, or 3; A device of claim 1, wherein the gate (11) is provided in a trench (20), the trench extending through the channel-accommodating region (15) into the drain drift region (14a).
6. (*Currently Amended*) A device of Claim 5 comprising a plurality of adjacent cells, each including a gate (11) in a trench (20), wherein a deep diffusion region (40) of the

second conductivity type is provided between adjacent trenches, the deep diffusion region (40) being doped to a greater extent than the channel accommodating region (15).

7. (*Currently Amended*) A device of Claim 5 wherein the lower boundary (30b) of the localized region (30,36) is above the bottom of the gate trenches.

8. (*Currently Amended*) A device of claim 1, 2 or 3 wherein the channel-accommodating region (15) is a region of an opposite, second conductivity type.

9. (*Currently Amended*) A method of manufacturing a semiconductor device including a semiconductor body (10) comprising a source region (13) and a drain region (14,14a) of a first conductivity type, having therebetween a channel-accommodating region (15), the drain region comprising a drain drift region (14a) and a drain contact region (14), with the drain drift region between the channel-accommodating region and the drain contact region, and the drain drift region being doped to a lesser degree than the drain contact region, and an insulated gate (11) separated from the channel-accommodating region (15) by a gate insulating layer (17), the method including the step of:

forming a localised region (30,36,50) in the drain drift region (14a) juxtaposed with the channel-accommodating region (15), the localized region (30,36,50) comprising alternating stripes (31,32) of the first conductivity type and a second, opposite conductivity type, which stripes extend laterally alongside the channel-accommodating region (15) and away from the gate (11).

10. (*Currently Amended*) A method of Claim 9 wherein the localised region (30,36,50) forming step comprises implanting a dopant of one of the first and second conductivity types, defining a striped mask (35) over the semiconductor body (10), and implanting a dopant of the other of the first and second conductivity types.